

CMXD2004

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH VOLTAGE
SILICON SWITCHING DIODES**



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD2004 type contains three (3) Isolated High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: X04

SUPERmini™



SOT-26 CASE

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Average Forward Current
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, tp=1.0µs
Peak Forward Surge Current, tp=1.0s
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V _R	240
V _{RRM}	300
I _O	200
I _F	225
I _{FRM}	625
I _{FSM}	4.0
I _{FSM}	1.0
P _D	350
T _J , T _{stg}	-65 to +150
θ _{JA}	357

UNITS

V
V
mA
mA
mA
A
A
mW
°C
°C/W

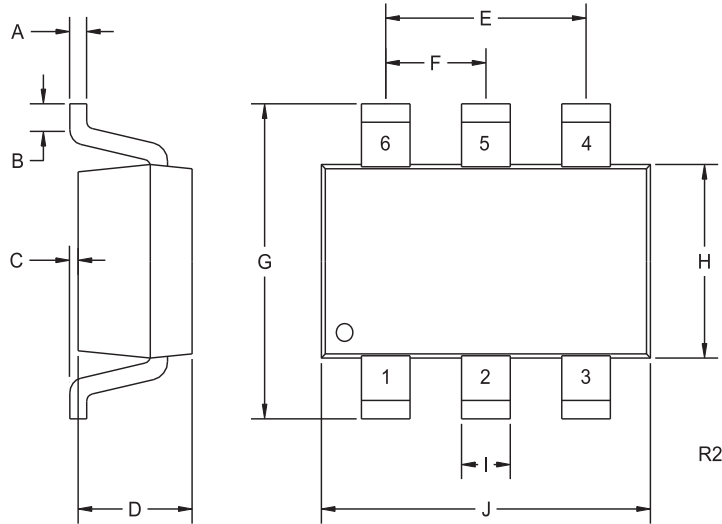
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I _R	V _R =240V		100	nA
I _R	V _R =240V, T _A =150°C		100	µA
BV _R	I _R =100µA	300		V
V _F	I _F =100mA		1.0	V
C _T	V _R =0, f=1.0MHz		5.0	pF
t _{rr}	I _F =I _R =30mA, I _{rr} =3.0mA, R _L =100Ω		50	ns

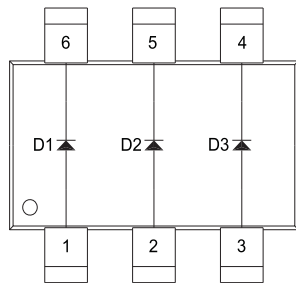
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SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

MARKING CODE: X04

R4 (9-February 2010)